

## AMENDMENTS

### In the Specification:

Amend the paragraph beginning at page 1, line 8, as follows:

With a switching circuit device that is employed for an antenna switching application in a third-generation cellular phone terminal, FETs (~~Filed~~ Field Effect transistors) must be serially connected in three stages in order to switch signals of approximately 26dBm. This switching circuit device is called an SPDT (Single Pole Double Throw), uses a total of six FETs, and has the five external terminals of a common input terminal IN, output terminals OUT1 and OUT2, and control terminals Ctl-1 and Ctl-2.

Amend the paragraph beginning at page 4, line 20, as follows:

The invention provides a switching circuit device that includes a first set of ~~filed~~ field effect transistors connected in series, a second set of ~~filed~~ field effect transistors connected in series, a common input terminal connected to a source electrode or a drain electrode of a transistor positioned at one end of the first set and connected to a source electrode or a drain electrode of a transistor positioned at one end of the second set, a first output terminal connected to a source electrode or a drain electrode of a transistor positioned at other end of the first set, a second output terminal connected to a source electrode or a drain electrode of a transistor positioned at other end of the second set, a first control terminal connected to gate electrodes of all the transistors of the first set, a second control terminal connected to gate electrodes of all the transistors of the second set, and a protecting element including an insulating region disposed between two high impurity concentration regions. The protecting element is connected between the source or drain electrode of the transistor positioned at the one end of the first set and the gate electrode of the transistor positioned at the one end of the first set, between the source or drain electrode of the transistor positioned at the one end of the second set and the gate electrode of the transistor positioned at the one end of the second set, between the source or drain electrode of the transistor connected to the first output terminal and the gate electrode of the transistor connected to the first output terminal, or between the source or drain electrode of the transistor connected to

the second output terminal and the gate electrode of the transistor connected to the second output terminal.

Amend paragraph beginning at page 5, line 8, as follows:

The invention also provides a switching circuit device that includes a first set of ~~field~~ field effect transistors connected in series and formed on a chip, a second set of ~~field~~ field effect transistors connected in series and formed on the chip, a common input terminal connected to a source electrode or a drain electrode of a transistor positioned at one end of the first set and connected to a source electrode or a drain electrode of a transistor positioned at one end of the second set, a first output terminal connected to a source electrode or a drain electrode of a transistor positioned at other end of the first set, a second output terminal connected to a source electrode or a drain electrode of a transistor positioned at other end of the second set, a first control terminal connected to gate electrodes of all the transistors of the first set, a second control terminal connected to gate electrodes of all the transistors of the second set, and a plurality of electrode pads formed on the chip. Each of the electrodes pads are connected to one of the terminals. The device also includes a high impurity concentration region formed at a periphery of each of the electrode pads. The electrode pad connected to the common input terminal and the electrode pad connected to a gate electrode of the transistor positioned at the one end of the first or second set are disposed at both sides of and adjacent a narrow insulating region, or the electrode pad connected to the first or second output terminal and the electrode pad connected to a gate electrode of a corresponding transistor positioned at the other end of the first or second set are disposed at both sides of and adjacent another narrow insulating region.

Amend the paragraph beginning at page 5, line 26, as follows:

The invention further provides a switching circuit device that includes a series of ~~field~~ field effect transistors formed on a substrate and connected in series, an input electrode pad disposed on the substrate and connected to a source electrode or a drain electrode of a transistor positioned at one end of the series, an output electrode pad disposed on the substrate and connected to a source electrode or a drain electrode of a transistor positioned at other end of the

series, a first control electrode pad disposed on the substrate and connected to a gate electrode of the transistor at the one end of the series, and a second control electrode pad disposed on the substrate and connected to a gate electrode of the transistor at the other end of the series. The second control electrode pad is connected to the first control electrode pad. The device also includes a high impurity concentration region formed in the substrate and at a peripheral portion of each of the electrode pads. The input electrode pad and the first control electrode pad are disposed so that the high impurity concentration regions of the input electrode pad and the first control electrode pad face each other and are separated by a first thin portion of the substrate, or the output electrode pad and the second control electrode pad are disposed so that the high impurity concentration regions of the output electrode pad and the second control electrode pad face each other and are separated by a second thin portion of the substrate.